

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	311	"sih.sub.4" near "sih.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/23 14:40
S2	217	"sih.sub.4" near "sih.sub.2" and vapor adj deposition	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:38
S3	101	"sih.sub.4" near "sih.sub.2" and vapor adj deposition and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/23 15:06
S4	8	("5378541").URPN.	USPAT	OR	ON	2005/06/23 14:45
S5	191	(silane "sih.sub.4") near ("h.sub.2" hydrogen) same vapor adj deposition same plasma	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:39
S10	515	(silane "sih.sub.4") with ("h.sub.2" hydrogen) and 427/255\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/23 15:50
S11	26	(silane "sih.sub.4") with ("h.sub.2" hydrogen) and 427/255\$.ccls. and microcrystalline	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:36
S12	670	(silane "sih.sub.4") with ("h.sub.2" hydrogen) and plasma near3 (vapor adj deposition cvd) and microcrystalline	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 09:45
S13	275	(silane "sih.sub.4") with ("h.sub.2" hydrogen) and plasma near3 (vapor adj deposition cvd) and microcrystalline and (repeat\$3 build\$1up)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 09:46
S14	86	(silane "sih.sub.4") with ("h.sub.2" hydrogen) and plasma near3 (vapor adj deposition cvd) with microcrystalline and (repeat\$3 build\$1up)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 09:52
S15	28	(Tsujimura tokuda).in. and (silane)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 09:49
S16	4	(Tsujimura.in. tokuda.in.) and microcrystalline	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 11:14

S17	58	(silane "sih.sub.4") with ("h.sub.2" hydrogen) and plasma near3 (vapor adj deposition cvd) with microcrystalline and (repeat\$3 build\$1up) and i-type	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:36
S18	7	("5686349").URPN.	USPAT	OR	ON	2005/06/24 10:09
S19	48	(Tsujimura.in. tokuda.in.) and plasma near4 (vapor adj deposition cvd)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 11:15
S20	1	(Tsujimura.in. tokuda.in.) and plasma near4 (vapor adj deposition cvd) and (silane "sih. sub.4") with ("h.sub.2" hydrogen)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/06/24 11:15
S21	2	"sih.sub.4" near "sih.sub.2" and 427/96.8.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:38
S22	26	(silane "sih.sub.4") near ("h.sub.2" hydrogen) same vapor adj deposition and 427/255.7,255.23, 248.1,96.8,255.15,255.28,458, 588.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/07/13 12:43